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LIST OF DOCUMENTS CITED BY APPLICANT
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Applicants:

Kevin J. Linthicum, et al.

Filing Date:

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U.S. PATENT DOCUMENTS

Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
gm	1	Re. 34,861	02/14/95	Davis et al.	437	100	
	2	6,153,010	11/28/00	Koyoku et al.	117	95	
	3	6,100,111	08/08/00	Konstantinov	438	92	
	4	6,100,104	08/08/00	Haerle	438	33	
	5	6,051,849	04/08/00	Davis	257	103	
	6	6,051,849	04/08/00	Davis	257	103	
	7	5,915,194	06/22/99	Powell et al.	438	478	
	8	5,912,477	06/15/99	Negley	257	95	
	9	5,880,485	03/09/99	Marx et al.	257	94	
	10	5,877,070	03/02/99	Goesele et al.	438	458	
	11	5,815,520	09/29/98	Furushima	372	45	
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	14	5,760,426	06/02/98	Marx et al.	257	190	
	15	5,710,057	01/20/98	Kenney	437	62	
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	18	5,389,571	02/14/95	Takeuchi et al.	437	133	
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	37	11-145516	05/28/99	Japan			X (Abstract)
	38	WO 98/47170	10/22/98	PCT			
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gm	50	JP 8-125251	05/17/96	Japan			X (Abstract)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete If Known	
		Application Number	10/633,952
Sheet 1 of		Filing Date	August 4, 2003
		First Named Inventor	Linthicum, Kevin J.
		Art Unit	2815
		Examiner Name	Jerome Jackson, Jr.
		Attorney Docket Number	013921-000025

U.S. PATENT DOCUMENTS						
Examiner Initials [*]	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
GA	AA	5,633,192		05-27-97	Moustakas et al.	
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NON PATENT LITERATURE DOCUMENTS			
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Examiner Signature	<i>[Signature]</i>	Date Considered	11/5/04
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